

Substitute for form 1449 A & B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	Not Assigned
				Confirmation Number	Not Assigned
				Filing Date	April 02, 2002
				First Named Inventor	Joel JACQUET
				Art Unit	Not Assigned
Examiner Name	Not Assigned	Attorney Docket Number	Q68831		
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
TN		US 5,363,397		11/08/94	Collins et al
TN		US 4,839,308		06/13/89	Fye

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
TN		Y. Uenishi et al, "Tunable laser Diode Using a Nickel Micromachined External Mirro", ELECTRONICS LETTERS, IEE Stevenage, Great Britain, Vol. 32, No. 13, June 20, 1996, pp. 1207-1208, XP000965745 ✓	Yes
TN		T. Baba et al, "A Novel Short-Cavity Laser with Deep-Grating Distributed Bragg Reflectors", JAPANESE JOURNAL OF APPLIED PHYSICS, PUBLICATION OFFICE JAPANESE JOURNAL OF APPLIED PHYSICS, Tokyo, Japan, Vol. 35, No. 2B, February 1, 1996, pp. 1390-1394, XP000701047 ✓	
I		PATENT ABSTRACTS OF JAPAN, Vol. 1998, No. 2, January 30, 1998 corresponding to JP 09 260768 A (Nippon Telegr & Amp..) dated October 3, 1997 ✓	
I		"Embedded Semiconductor Laser with Anti-Reflection coatings", IBM TECHNICAL DISCLOSURE BULLETIN, US, NY, Vol. 34, No. 5, October 1, 1991, pp. 141-142, XP000189657 ✓	
I		E. Hoeffling et al, "Edge-Emitting Gainas-AlGaas Microlasers", IEEE PHOTONICS TECHNOLOGY LETTERS, IEEE, Inc. New York, US, Vol. 11, No. 8, August 1999, pp. 943-945, XP000860958 ✓	

Examiner Signature	<i>Tuan Nguyen</i>	Date Considered	12/7/02
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.